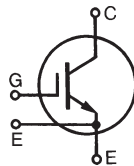


# High Voltage IGBT

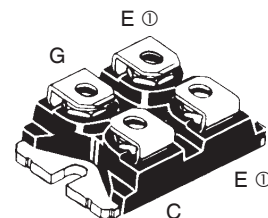
## IXGN100N170

$V_{CES} = 1700V$   
 $I_{C90} = 95A$   
 $V_{CE(sat)} \leq 3.0V$



SOT-227B, miniBLOC

E153432



G = Gate, C = Collector, E = Emitter  
 ① either emitter terminal can be used as Main or Kelvin Emitter

Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $150^\circ C$	1700	V
$V_{CGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GE} = 1M\Omega$	1700	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$	160	A
$I_{C90}$	$T_C = 90^\circ C$	95	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	600	A
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 125^\circ C$ , $R_G = 1\Omega$ Clamped Inductive Load	$I_{CM} = 200$ @ $0.8 \cdot V_{CES}$	A
$t_{sc}$ <b>(SCSOA)</b>	$V_{GE} = 15V$ , $V_{CE} = 1250V$ , $T_J = 125^\circ C$ $R_G = 10\Omega$ , Non Repetitive	10	$\mu s$
$P_C$	$T_C = 25^\circ C$	735	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$V_{ISOL}$	50/60Hz $I_{ISOL} \leq 1mA$	$t = 1min$ $t = 1s$	2500 3000 V~ V~
$M_d$	Mounting Torque Terminal Connection Torque	1.5/13 1.3/11.5	Nm/lb.in. Nm/lb.in.
<b>Weight</b>		30	g

### Features

- Optimized for Low Conduction and Switching Losses
- Isolation Voltage 2500V~
- Short Circuit Capability
- International Standard Package
- High Current Handling Capability

### Advantages

- High Power Density
- Low Gate Drive Requirement

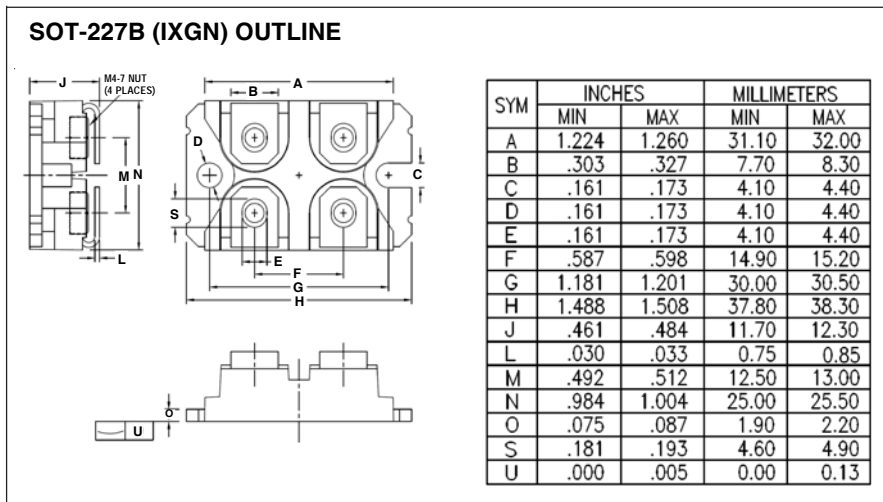
### Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Welding Machines

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 3mA$ , $V_{GE} = 0V$	1700		V
$V_{GE(th)}$	$I_C = 8mA$ , $V_{CE} = V_{GE}$	3.0		V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ $T_J = 125^\circ C$			50 $\mu A$ 3 mA
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 200$ nA
$V_{CE(sat)}$	$I_C = 100A$ , $V_{GE} = 15V$ , Note 1		2.5	3.0 V

Symbol Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 60\text{A}, V_{CE} = 10\text{V}$ , Note 1	36	64	S
$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		9200	pF
$C_{oes}$			455	pF
$C_{res}$			150	pF
$Q_g$	$I_C = 100\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		425	nC
$Q_{ge}$			65	nC
$Q_{gc}$			186	nC
$t_{d(on)}$	<b>Resistive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 100\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 1\Omega$		35	ns
$t_r$			192	ns
$t_{d(off)}$			285	ns
$t_f$			395	ns
$t_{d(on)}$	<b>Resistive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = 100\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 1\Omega$		35	ns
$t_r$			250	ns
$t_{d(off)}$			285	ns
$t_f$			435	ns
$R_{thJC}$				0.17 $^\circ\text{C/W}$
$R_{thCS}$		0.05		$^\circ\text{C/W}$

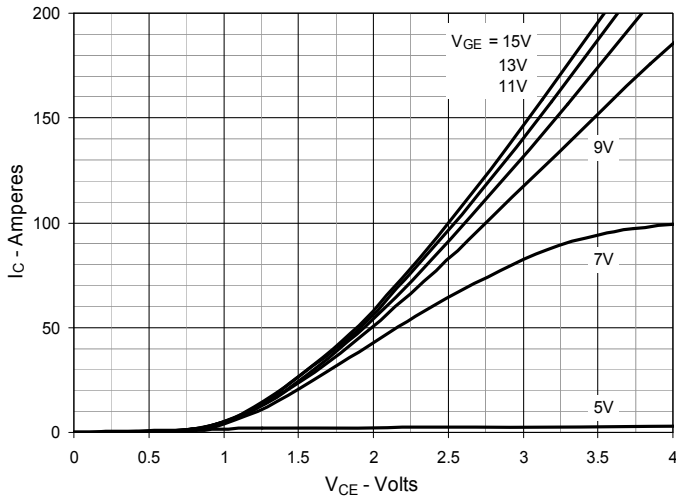
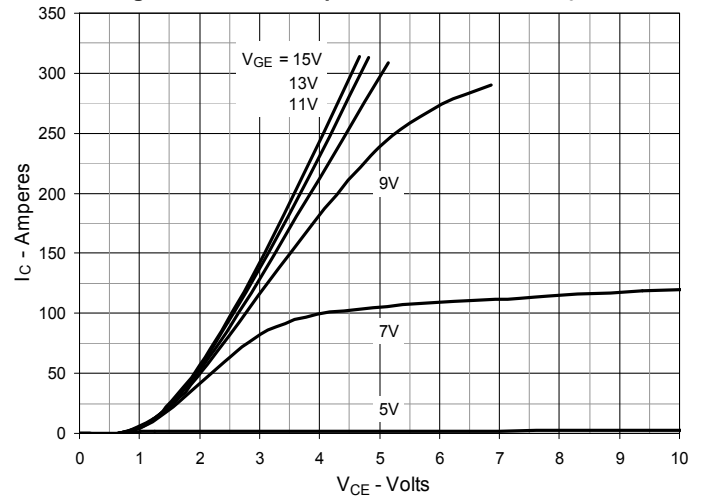
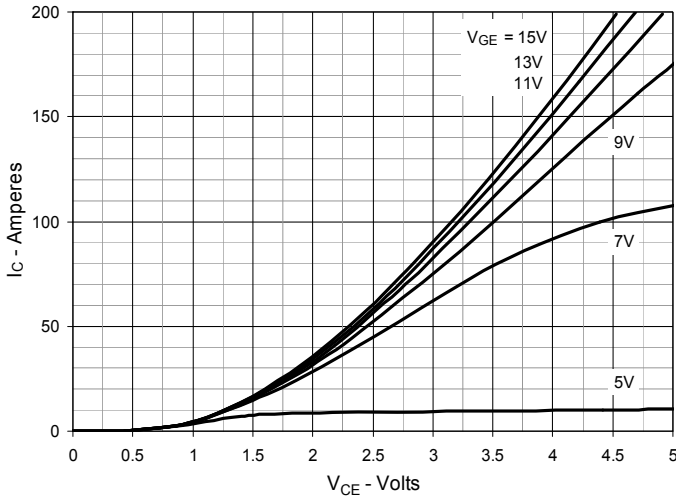
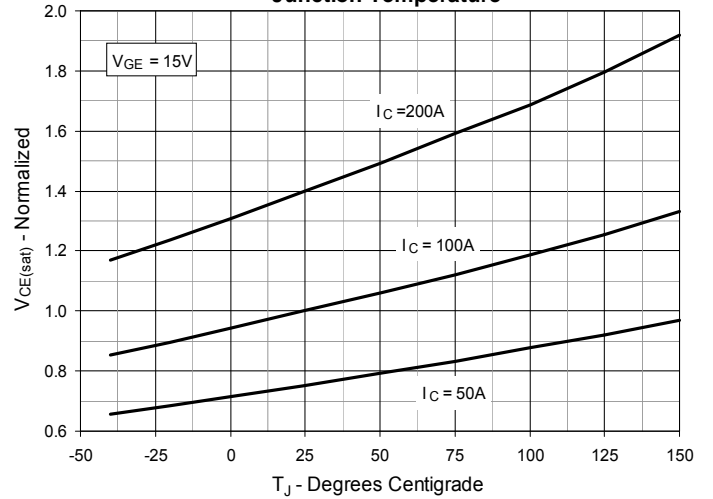
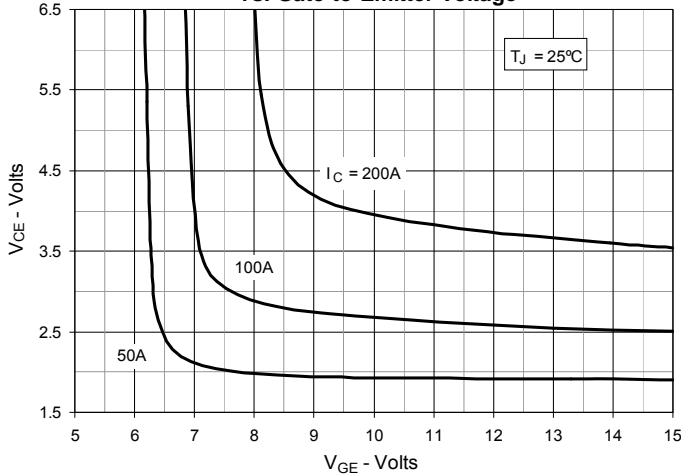
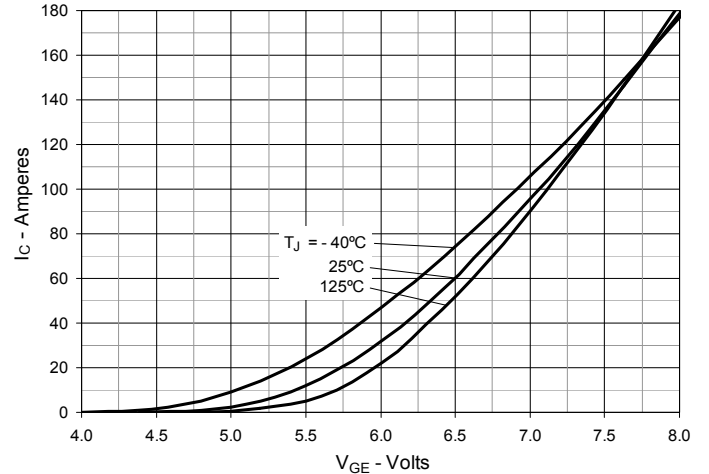
Note: 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

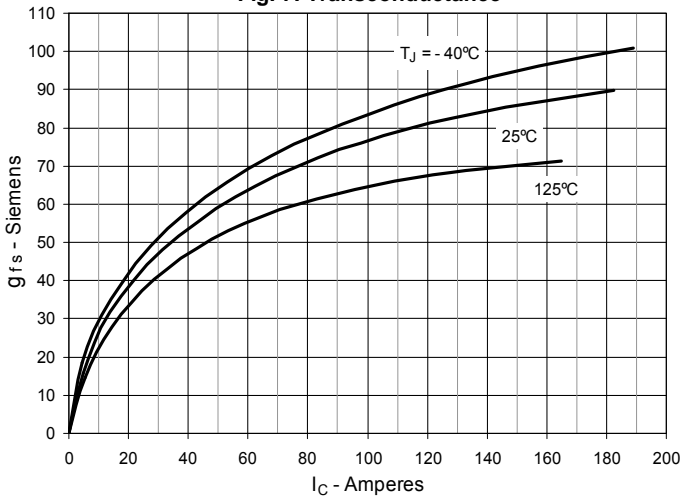
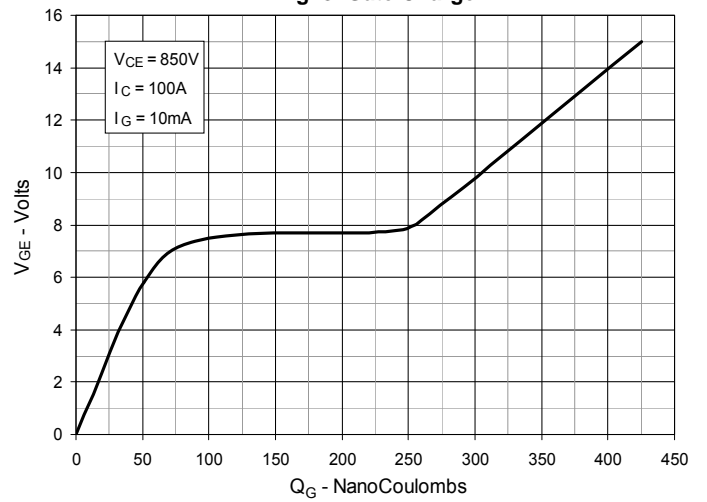
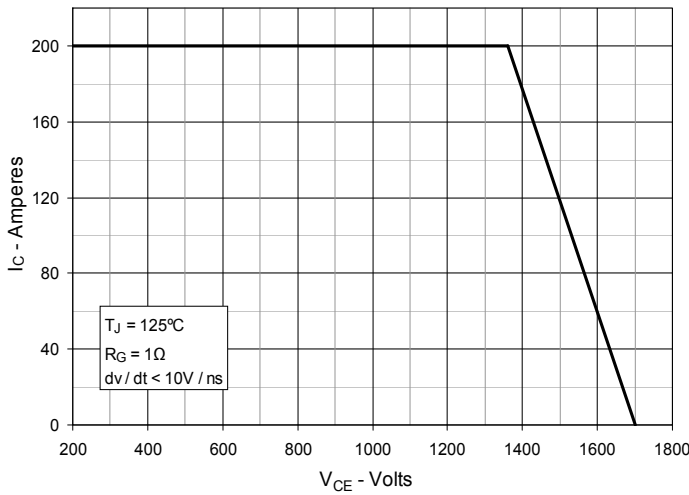
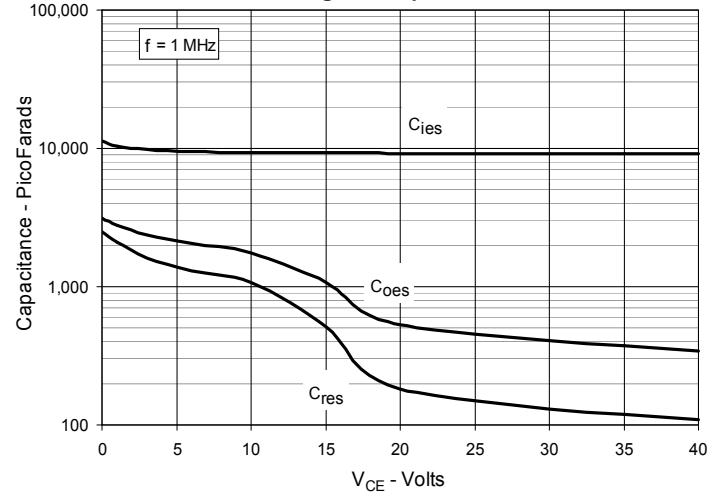
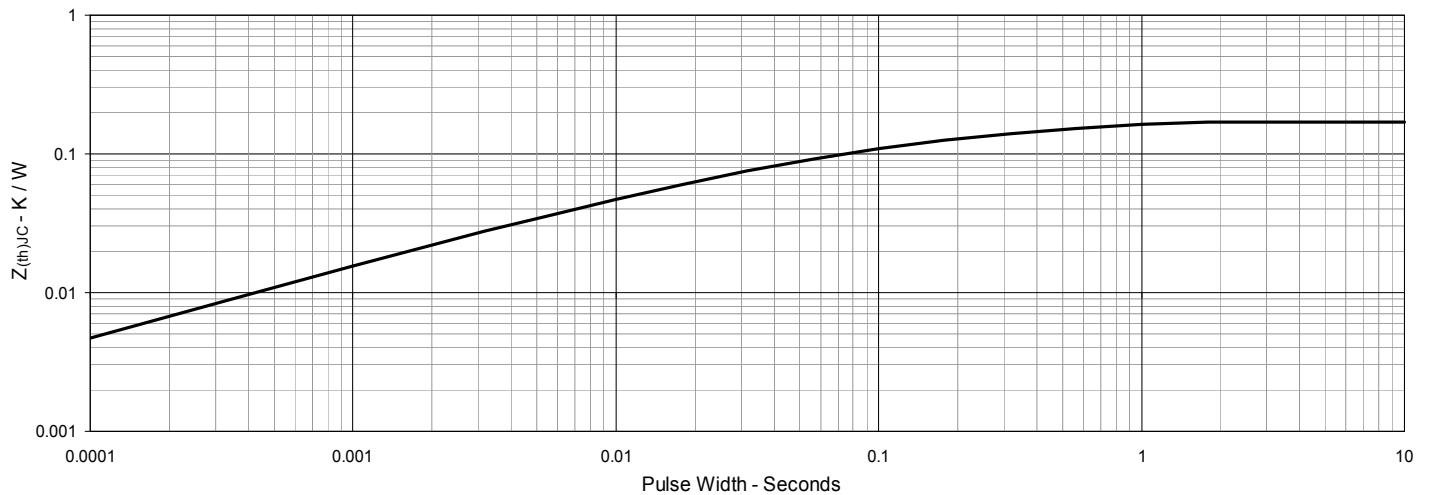


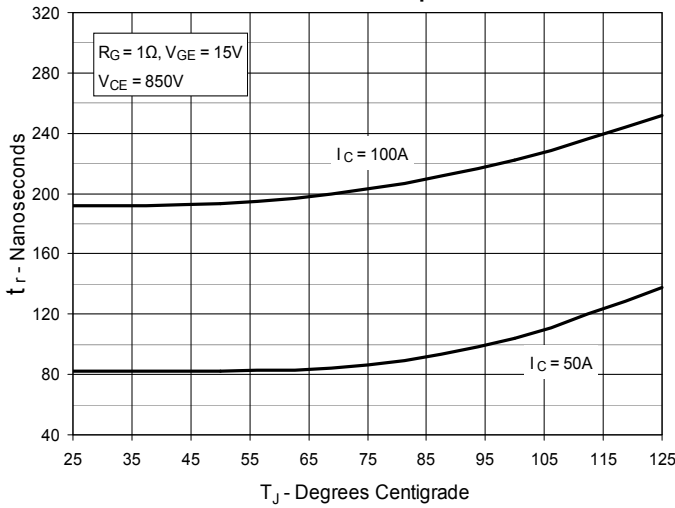
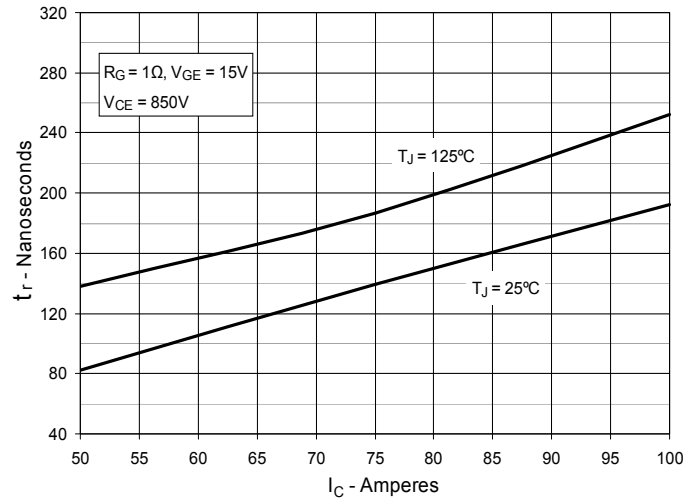
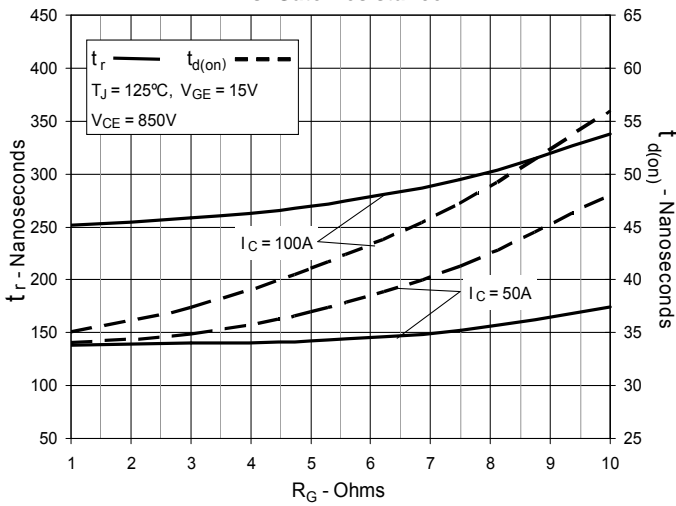
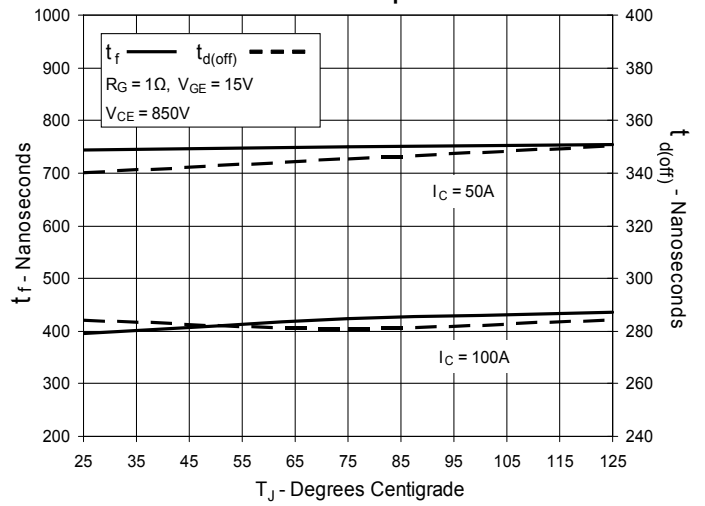
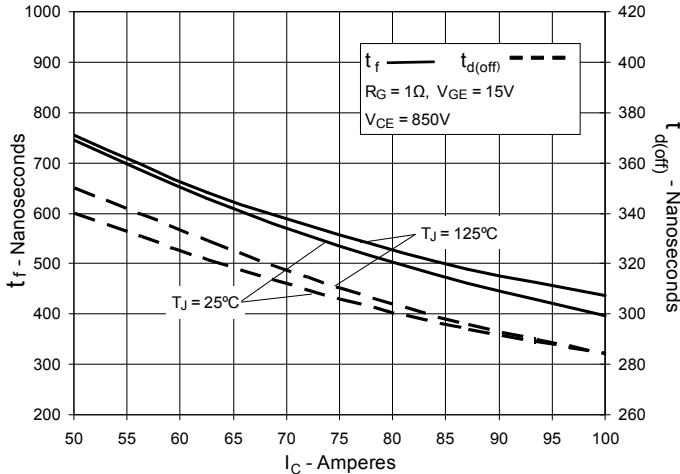
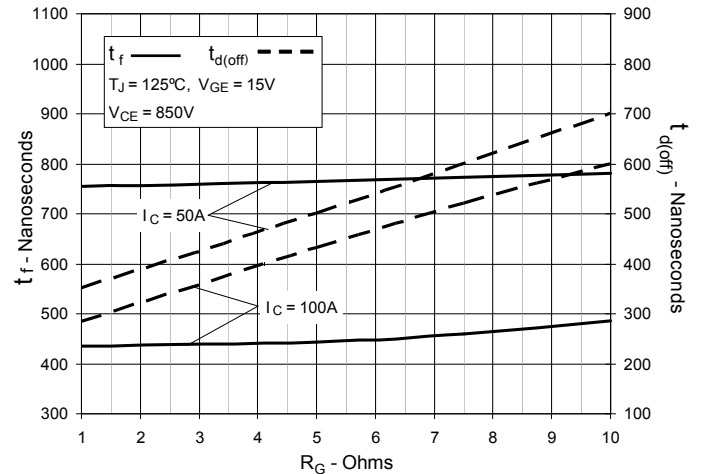
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$** 

**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**

**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**

**Fig. 6. Input Admittance**


**Fig. 7. Transconductance**

**Fig. 8. Gate Charge**

**Fig. 9. Reverse-Bias Safe Operating Area**

**Fig. 10. Capacitance**

**Fig. 11. Maximum Transient Thermal Impedance**


**Fig. 12. Resistive Turn-on Rise Time vs. Junction Temperature**

**Fig. 13. Resistive Turn-on Rise Time vs. Collector Current**

**Fig. 14. Resistive Turn-on Switching Times vs. Gate Resistance**

**Fig. 15. Resistive Turn-off Switching Times vs. Junction Temperature**

**Fig. 16. Resistive Turn-off Switching Times vs. Collector Current**

**Fig. 17. Resistive Turn-off Switching Times vs. Gate Resistance**




---

Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at [www.littelfuse.com/disclaimer-electronics](http://www.littelfuse.com/disclaimer-electronics).